

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-9. (Canceled)

10. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage ~~and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage~~ having a plurality of suction inlets;

~~fixing said substrate by a pusher;~~

flattening said substrate by vacuum-sucking ~~[[said]]~~ a lower surface of said substrate using said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

11. (Previously Presented) A method according to claim 10 wherein said laser beam is an excimer laser beam.

12. (Previously Presented) A method according to claim 10 wherein said semiconductor device is a liquid crystal display device.

13-15. (Canceled)

16. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;
heating said semiconductor film;
setting said substrate onto a stage ~~and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage~~ having a plurality of suction inlets;
~~fixing said substrate by a pusher;~~
flattening said substrate by vacuum-sucking ~~[[said]]~~ a lower surface of said substrate using said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

17. (Previously Presented) A method according to claim 16 wherein said laser beam is an excimer laser beam.

18. (Previously Presented) A method according to claim 16 wherein said semiconductor device is a liquid crystal display device.

19-21. (Canceled)

22. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;
heating said substrate to crystallize said semiconductor film;
setting said substrate onto a stage ~~and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage~~ having a plurality of suction inlets;
~~fixing said substrate by a pusher;~~

flattening said substrate by vacuum-sucking [[said]] a lower surface of said substrate
using said plurality of suction inlets; and

irradiating the crystallized semiconductor film with a laser beam having a cross section
which is elongated in one direction while relatively moving said substrate with respect to said
laser beam, and while vacuum-sucking said lower surface of said substrate.

23. (Previously Presented) A method according to claim 22 wherein said laser beam is an
excimer laser beam.

24. (Previously Presented) A method according to claim 22 wherein said semiconductor
device is a liquid crystal display device.

25. (Previously Presented) A method of manufacturing a liquid crystal display device
comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;
heating said substrate and said semiconductor film, wherein said heating deforms said
substrate and said semiconductor film from flat to curved;
flattening said substrate by cooling; and
irradiating said semiconductor film with a laser beam having a cross section which is
elongated in one direction while relatively moving said substrate with respect to said laser beam.

26. (Previously Presented) A method according to claim 25 wherein said laser beam is an
excimer laser beam.

27. (Previously Presented) A method according to claim 25 wherein at least a part of the
flattened substrate constitutes the liquid crystal display device.

28. (Previously Presented) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;
heating said substrate to crystallize said semiconductor, wherein said heating deforms said substrate and said semiconductor film from flat to curved;
flattening said substrate by cooling; and
irradiating the crystallized semiconductor film with a laser beam.

29. (Previously Presented) A method according to claim 28 wherein said laser beam is an excimer laser beam.

30. (Previously Presented) A method according to claim 28 wherein at least a part of the flattened substrate constitutes the liquid crystal display device.

31-37. (Canceled)

38. (Previously Presented) A method according to claim 10 wherein said substrate is a glass substrate.

39. (Canceled)

40. (Previously Presented) A method according to claim 16 wherein said substrate is a glass substrate.

41. (Canceled)

42. (Previously Presented) A method according to claim 22 wherein said substrate is a glass substrate.

43. (Previously Presented) A method according to claim 25 wherein said substrate is a glass substrate.

44. (Previously Presented) A method according to claim 28 wherein said substrate is a glass substrate.

45. (Canceled)

46. (Previously Presented) A method according to claim 10 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

47. (Canceled)

48. (Previously Presented) A method according to claim 16 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

49. (Canceled)

50. (Previously Presented) A method according to claim 22 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

51. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage ~~in such a manner that a lower surface of said substrate is in contact with said stage~~ having a plurality of suction inlets;

~~fixing said substrate by a pusher;~~

flattening said substrate by vacuum-sucking ~~[[said]]~~ a lower surface of said substrate
using said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam while relatively moving said
substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said
substrate.

52. (Previously Presented) A method according to claim 51 wherein said laser beam is an
excimer laser beam.

53. (Previously Presented) A method according to claim 51 wherein an entire surface of
said semiconductor film is irradiated by said laser beam.

54. (Previously Presented) A method according to claim 51 wherein said substrate is a
glass substrate.

55. (Previously Presented) A method according to claim 51 wherein said semiconductor
device is a liquid crystal display device.

56. (Currently Amended) A method of manufacturing a semiconductor device comprising
the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage ~~in such a manner that a lower surface of said substrate~~
~~is in contact with said stage~~ having a plurality of suction inlets;

~~fixing said substrate by a pusher;~~

flattening said substrate by vacuum-sucking ~~[[said]]~~ a lower surface of said substrate
using said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

57. (Previously Presented) A method according to claim 56 wherein said laser beam is an excimer laser beam.

58. (Previously Presented) A method according to claim 56 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

59. (Previously Presented) A method according to claim 56 wherein said substrate is a glass substrate.

60. (Previously Presented) A method according to claim 56 wherein said semiconductor device is a liquid crystal display device.

61. (Canceled)

62. (Previously Presented) A method according to claim 10 wherein said stage has a surface roughness of 5 μm or less.

63. (Canceled)

64. (Previously Presented) A method according to claim 16 wherein said stage has a surface roughness of 5 μm or less.

65. (Canceled)

66. (Previously Presented) A method according to claim 22 wherein said stage has a surface roughness of 5 μm or less.

67. (Previously Presented) A method according to claim 51 wherein said stage has a surface roughness of 5 μm or less.

68. (Previously Presented) A method according to claim 56 wherein said stage has a surface roughness of 5 μm or less.

69. (New) A method according to claim 10 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

70. (New) A method according to claim 16 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

71. (New) A method according to claim 22 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

72. (New) A method according to claim 51 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

73. (New) A method according to claim 56 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.